

1N461A-1N464A

GENERAL PURPOSE, HIGH CONDUCTANCE SILICON DIODES

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

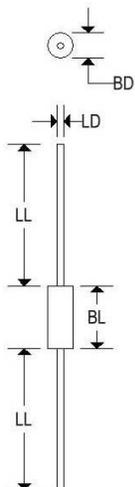
Ratings	Symbol	1N461A	1N462A	1N463A	1N464A	Unit
Working inverse voltage	WIV	25	60	175	125	V
Average rectified current	I_O	200	200	200	200	mA
Continuous forward current	I_F	500	500	500	500	mA
Peak repetitive forward current	i_f	600	600	600	600	mA
Peak forward surge current	$i_{f(surge)}$	1.0	1.0	1.0	1.0	A
Pulse width = 1s						
Pulse width = 1μs		4.0	4.0	4.0	4.0	

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Min	Max	Units
Forward voltage $I_F = 100\text{mA}$	V_F	-	1.0	V
Reverse current $V_R = \text{rated WIV}$ $V_R = \text{rated WIV}, T_A = 150^\circ\text{C}$	I_R	-	500	nA
		-	30	μA
Breakdown voltage $I_R = 1000\mu\text{A}$	BV	1N461A	30	-
		1N462A	70	-
		1N463A	200	-
		1N464A	150	-

MECHANICAL CHARACTERISTICS

Case	DO-35
Marking	Body painted, alpha-numeric
Polarity	Cathode band



	DO-35			
	Inches		Millimeters	
	Min	Max	Min	Max
BD	0.055	0.090	1.400	2.290
BL	0.120	0.200	3.050	5.080
LD	0.018	0.022	0.460	0.560
LL	1.000	1.500	25.400	38.100